TRANSISTOR MOS-FET IGBT DIODE

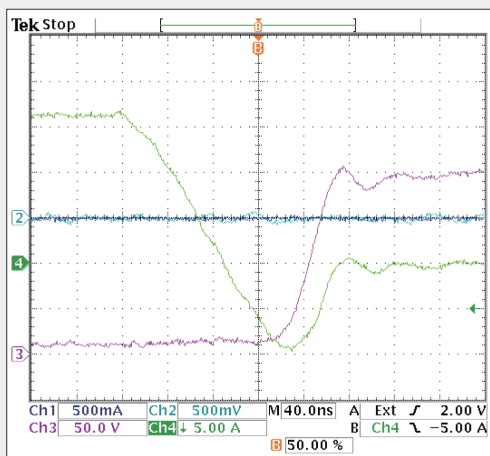
SEMICONDUCTOR DYNAMIC CHARACTERISTIC EVALUATION SYSTEM 半導体動特性評価システム

SWRL1510ZZ 1500V 1000A

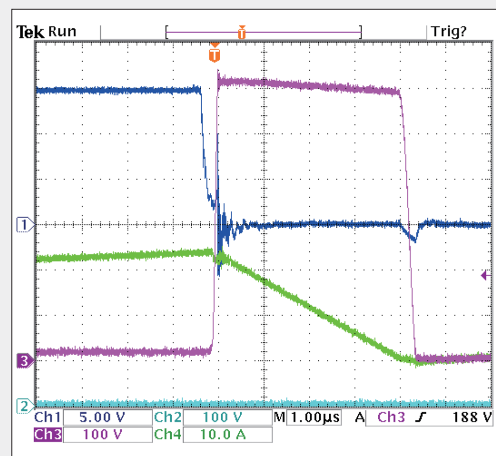
●SWRL1510ZZ has 1ms forcing function at 1500V, 1000A, which is enough power for power device dynamic characteristics tester. Measurement part is designed for testing in both low and high temperature. It can connect to external chamber to evaluate device by temperature characteristics.

●1500V, 1000Aで1msの印加性能を持っており、パワーデバイスの動特性試験として十分なパワーを備えています。測定部はデバイスを冷却または高温状態で測定できるような構造が考慮されており、外部チャンバーとの接続を可能とし、温度特性によるデバイス評価を可能としています。

Measurement Waveform (di/dt)



Measurement Waveform (Avalanche)



MODEL	SWRL1510ZZ
TEST ITEMS	
R-SWITCHING/L-SWITCHING	td(on), tr, td(off), tf, e(on), e(off), e(sw)
AVALANCHE	V_{SUS}, E_{AS}, E_{AP}, I_{DP}
di/dt	di/dt, I_{RP}, trr, Qrr
QG	Q_{GS}, Q_{Gd}, Q_{G}
SETTING RANGE	
MEASURABLE DEVICE	Transistor, MOS-FET, IGBT,Diode
MEASUREMENT RANGE	000ns~999μs
V_{DD}	10V~1500V 1V STEP
I_D (Limit)	10A~1000A 10A STEP
V_{GF}	0.0V~30.0V 0.1V STEP [Maximum pulse current 10A] [最大パルス電流10A]
V_{GR}	0.0V~30.0V 0.1V STEP [Maximum pulse current 10A] [最大パルス電流10A]
Rg	0.0Ω~99.9Ω 0.1Ω STEP
I_{BF}/I_{BR}	0.01A~3.00A 0.01A STEP
V-CLAMP	30V~1500V 1V STEP
Time-1	0.1μs~999.9μs 0.1μs STEP
Time-2	0.1μs~999.9μs 0.1μs STEP
Time-3	0.1μs~99.9μs 0.1μs STEP
I_G	0.1mA~99.9mA 0.1mV STEP
V_G-CLAMP	1V~25V 1V STEP
X-bias	0.01V~15.00V 0.01V STEP
I_M	1mA~200mA 1mA STEP
V_F	1mV~200mV 1mV STEP
BINNING	
OPEN /SHORT CHECK	V_{GF} ON : V_{DS}(V_{CE})＞V_{DD}×50%…OPEN V_{GF} OFF : V_{DS}(V_{CE})＜V_{DD}×50%…SHORT
BIN INDICATION	PASS, LIMIT-FAIL/CONTACT-FAIL, ERROR/DRIVE-FAIL, OPEN/SHORT
DIMENSIONS & WEIGHT	
SUPPLY UNIT	550(W)×870(D)×1700(H)…395kg
CONTROL UNIT	1200(W)×550(D)×1280(H)…235kg
MEASUREMENT UNIT	1200(W)×650(D)×840(H)…300kg